

LINEAR SYSTEMS

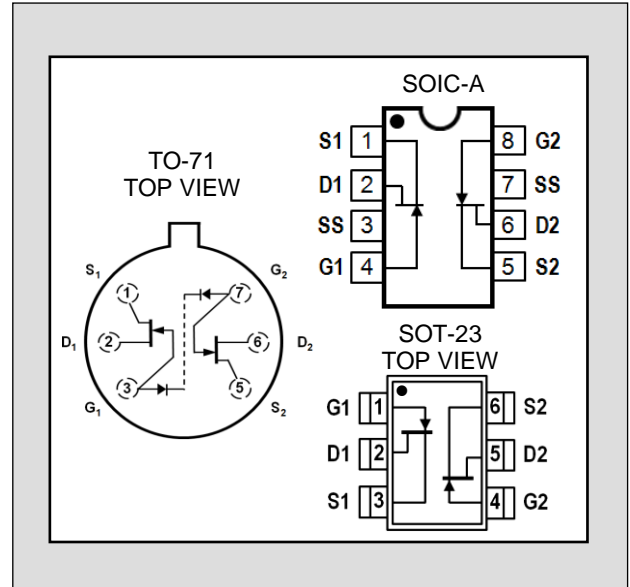
Twenty-Five Years Of Quality Through Innovation

LS843 LS844 LS845

ULTRA LOW NOISE LOW DRIFT
MONOLITHIC DUAL N-CANNEL JFET

FEATURES

ULTRA LOW NOISE	$e_n=3\text{nV}/\text{Hz}$ TYP.
LOW LEAKAGE	$I_G=15\text{pA}$ TYPs.
LOW DRIFT	$ V_{GS1-2}/T = 5\mu\text{V}/^\circ\text{C}$ max.
ULTRA LOW OFFSET VOLTAGE	$ V_{GS1-2} = 1\text{mV}$ max.
ABSOLUTE MAXIMUM RATINGS¹	
@ 25°C (unless otherwise noted)	
Maximum Temperatures	
Storage Temperature	-55° to +150°C
Operating Junction Temperature	-55° to +150°C
Maximum Voltage and Current for Each Transistor¹	
-V _{GSS}	Gate Voltage to Drain or Source 60V
I _{G(f)}	Gate Forward Current 50mA
Maximum Power Dissipation²	
Device Dissipation ² @ Free Air - Total	400mW T _A =+25°C

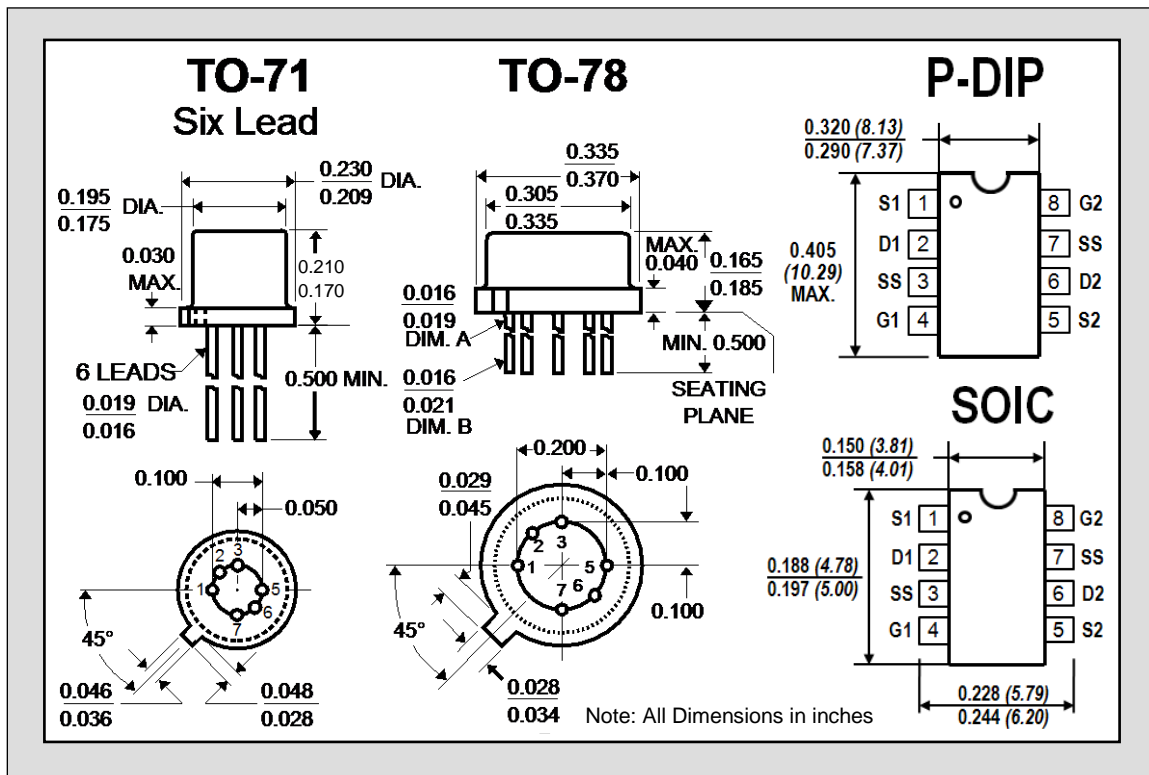


ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	LS843	LS844	LS845	UNITS	CONDITIONS
$ V_{GS1-2}/T $ max.	Drift vs. Temperature	5	10	25	$\mu\text{V}/^\circ\text{C}$	$V_{DG} = 10\text{V}$ $I_D = 500\mu\text{A}$ $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$
$ V_{GS1-2} $ max.	Offset Voltage	1	5	15	mV	$V_{GS} = 10\text{V}$ $I_D = 500\mu\text{A}$

SYMBOL	CHARACTERISTIC ³	MIN.	TYP.	MAX.	UNITS	CONDITIONS
BV _{GSS}	Breakdown Voltage	-60	--	--	V	$V_{DS} = 0$ $I_D = -1\text{nA}$
BV _{GGO}	Gate-to-Gate Breakdown	± 60	--	--	V	$I_{GGO} = \pm 1\mu\text{A}$ $I_D = 0$ $I_S = 0$
TRANSCONDUCTANCE						
G _{fss}	Full Conduction	1500	--	--	μS	$V_{DS} = 15\text{V}$ $V_{GS} = 0$ $f = 1\text{kHz}$
G _{fs}	Typical Conduction	1000	1500	--	μS	$V_{DS} = 15\text{V}$ $I_D = 500\mu\text{A}$
$ G_{fs1-2}/G_{fs1} $	Mismatch	--	0.6	3	%	
DRAIN CURRENT						
I _{DSS}	Full Conduction	1.5	5	15	mA	$V_{DS} = 15\text{V}$ $V_{GS} = 0$
$ I_{DSS1-2}/I_{DSS} $	Mismatch at Full Conduction	--	1	5	%	
GATE VOLTAGE						
V _{GS(off)}	Pinchoff Voltage	-1	--	-3.5	V	$V_{DS} = 15\text{V}$ $I_D = 1\text{nA}$
V _{GS}	Operating Range	-0.5	--	-3.5	V	$V_{DS} = 15\text{V}$ $I_D = 500\mu\text{A}$
GATE CURRENT						
-I _G	Operating	--	15	50	pA	$V_{DG} = 15\text{V}$ $I_D = 500\mu\text{A}$
-I _G	High Temperature	--	--	50	nA	$V_{DG} = 15\text{V}$ $I_D = 500\mu\text{A}$ $T_A = +125^\circ\text{C}$
-I _G	Reduced VDG	--	5	30	pA	$V_{DG} = 3\text{V}$ $I_D = 500\mu\text{A}$
-I _{GSS}	At Full Conduction	--	--	100	pA	$V_{GS} = 15\text{V}$ $V_{GS} = 0$

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNITS	CONDITIONS
	OUTPUT CONDUCTANCE					
G_{OSS}	Full Conduction	--	--	40	μS	$V_{DS}= 15V$ $V_{GS}= 0$
G_{OS}	Operating	--	2.0	2.7	μS	$V_{DS}= 15V$ $I_D= 200\mu A$
$ G_{OS1-2} $	Differential	--	0.02	0.2	μS	
	COMMON MODE REJECTION					
CMRR	$-20 \log \Delta V_{GS1-2}/ \Delta V_{DS} $	90	100	--	dB	$V_{DS}= 10$ to $20V$ $I_D= 500\mu A$
CMRR		--	85	--	dB	$V_{DS}= 5$ to $10V$ $I_D= 500\mu A$
	NOISE					
NF	Figure	--	--	0.5	dB	$V_{DS}= 15V$ $V_{GS}= 0$ $R_G= 10M\Omega$ $f= 100Hz$ $NBW= 6Hz$
e_n	Voltage	--	--	7	nV/Hz	$V_{DS}= 15V$ $I_D= 500\mu A$ $f= 1kHz$ $NBW= 1Hz$
e_n	Voltage	--	--	11	nV/Hz	$V_{DS}= 15V$ $I_D= 500\mu A$ $f= 10Hz$ $NBW= 1Hz$
	CAPACITANCE					
C_{ISS}	Input	--	--	8	pF	$V_{DS}= 15V$ $I_D= 500\mu A$ $f= 1mHz$
C_{RSS}	Reverse Transfer	--	--	3	pF	
C_{DD}	Drain-to-Drain	--	0.5	--	pF	$V_{DD}= 15V$ $I_D= 500\mu A$ $f= 1mHz$



NOTES:

1. These ratings are limiting values above which the serviceability of any semiconductor may be impaired
2. Derate 4mW/°C above 25°C
3. All MIN/TYP/MAX limits are absolute numbers. Negative signs indicate electrical polarity only.

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